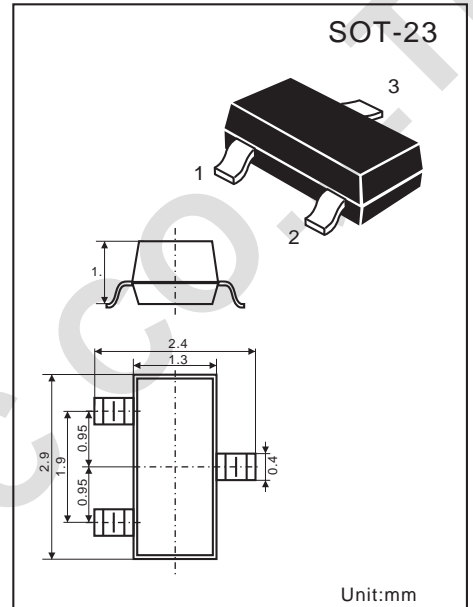
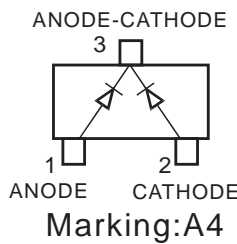


SWITCHING DIODE

Features

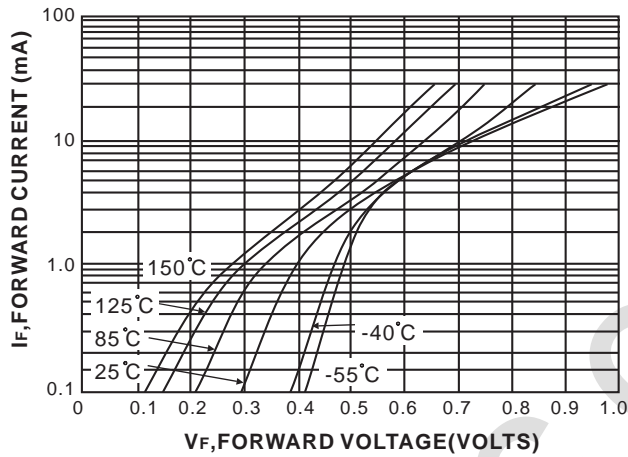
- Power dissipation
 $P_D : 225 \text{ mW (} T_{amb}=25^\circ \text{C)}$
- Pluse Drain
 $I_F : 200 \text{ mA}$
- Reverse Voltage
 $V_R : 70\text{V}$
- Operating and storage junction temperature range
 $T_j, T_{stg} : -55^\circ \text{C to } +150^\circ \text{C}$



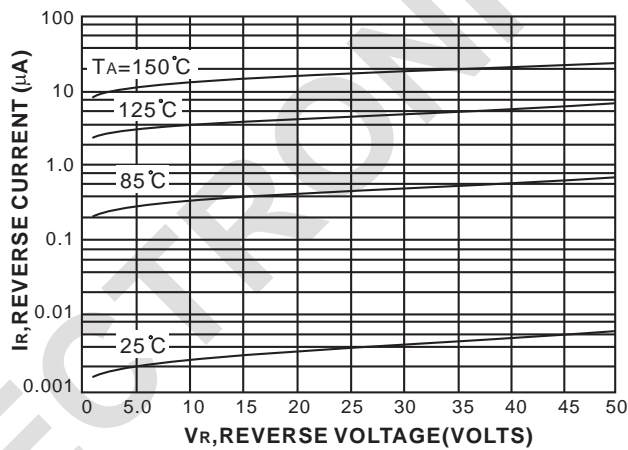
Electro-Optical Characteristics

($T_a=25^\circ \text{C}$)

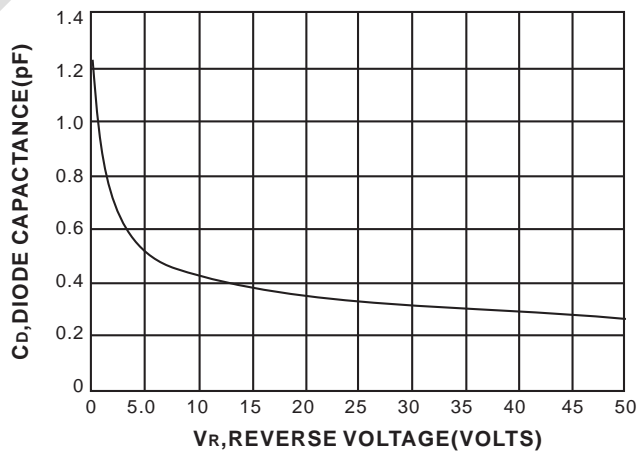
Parameter	Symbol	Test Condition	MIN.	MAX.	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	70		V
Reverse Voltage leakage current	I_R	$V_R=70\text{V}$		2.5	μA
Forward Voltage	V_F	$I_F=1\text{mA}$		715	mV
		$I_F=10\text{mA}$		855	
		$I_F=50\text{mA}$		1000	
		$I_F=150\text{mA}$		1250	
Diode Capacitance	C_D	$V_R=0\text{V } f=1\text{MHz}$		1.5	pF
Reverse Recovery Time	t_{rr}	$I_F=I_R=10\text{mA}$ $I_R=1\text{mA } V_R=5\text{V}$ $R_C=100\Omega$		6	nS



Forward Voltage



Reverse Current Versus Reverse Voltage



Typical Capacitance